
ERRATA

Equilibrium Shape of Si
[Phys. Rev. Lett. 70, 1643 (1993)]

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The Si step energy of 28 ± 10 meV/atom determined from the curvature of small voids near (100) should more properly be compared with half of the double *A*-type step energy (i.e., 0.5×50 meV/atom [1]), as opposed to the single *B*-type step energy (23 meV/atom) used in this paper. The authors would like to thank Dr. H. J. W. Zandvliet for pointing this out.

[1] D. J. Chadi, Phys. Rev. Lett. **59**, 1691 (1987).

Singular Behavior of Shear Flow Far from Equilibrium
[Phys. Rev. Lett. 71, 3971 (1993)]

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The matrix \mathcal{L} given by Eq. (13) has two misprints: the element (5,9) should be $-\frac{12}{7}a$ rather than $\frac{12}{7}a$ and the element (7,6) should be a rather than $-a$. The results reported in the paper have been obtained from the correct matrix \mathcal{L} .

The numerical value given in the paper for the diagonal element $c_3(a)$ is based on numerical calculations done by Ikenberry and Truesdell [J. Rat. Mech. Anal. **5**, 1 (1956)]. A more accurate evaluation [Z. Alterman, K. Frankowski, and C. L. Pekeris, Astrophys. J. Suppl. Ser. **7**, 291 (1962/3)] yields $c_3(a) = 4\alpha(a) + 1.873\nu$, which leads to a modified value for the critical shear rate: $a_c \approx 6.845\nu$.

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Surface-Tension-Gradient-Induced Pattern Formation in Monolayers
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We regret that there was a misspelling on the name of the last author. It should be H. Ringsdorf. The correct names of the authors should read as follows: Mu Wang, G. Wildburg, J. H. van Esch, P. Bennema, R. J. M. Nolte, and H. Ringsdorf.